

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TRW53601** is Designed for General Purpose Oscillator Applications up to 2.3 GHz.

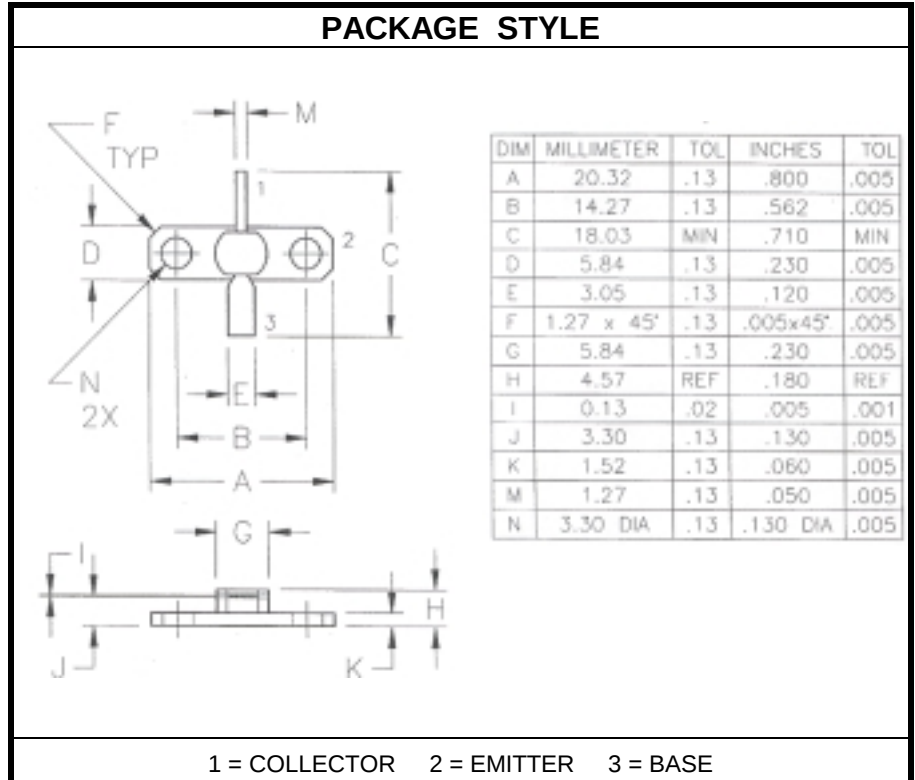
FEATURES:

- Diffused Ballast Resistors
- **Omnigold™** Metalization System
- Common Emitter

MAXIMUM RATINGS

I_C	400 mA
V_{CES}	50 V
P_{DISS}	3.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	31 $^\circ\text{C/W}$

PACKAGE STYLE



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$	20			V
BV_{CES}	$I_C = 10\text{ mA}$	50			V
BV_{CBO}	$I_C = 1.0\text{ mA}$	45			V
BV_{EBO}	$I_E = 250\text{ }\mu\text{A}$	3.5			V
I_{CBO}	$V_{CB} = 28\text{ V}$			0.25	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	15		120	---
C_{OB}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			3.5	pF
P_O	$V_{CE} = 20\text{ V}$ $I_E = 120\text{ mA}$ $f = 2.0\text{ GHz}$	.8			W
IMD	$P_{IN} = .100\text{ W}$		-30		dB
G_p		8.5	9.5		dB
VSWR		∞			